

TOPF 4360

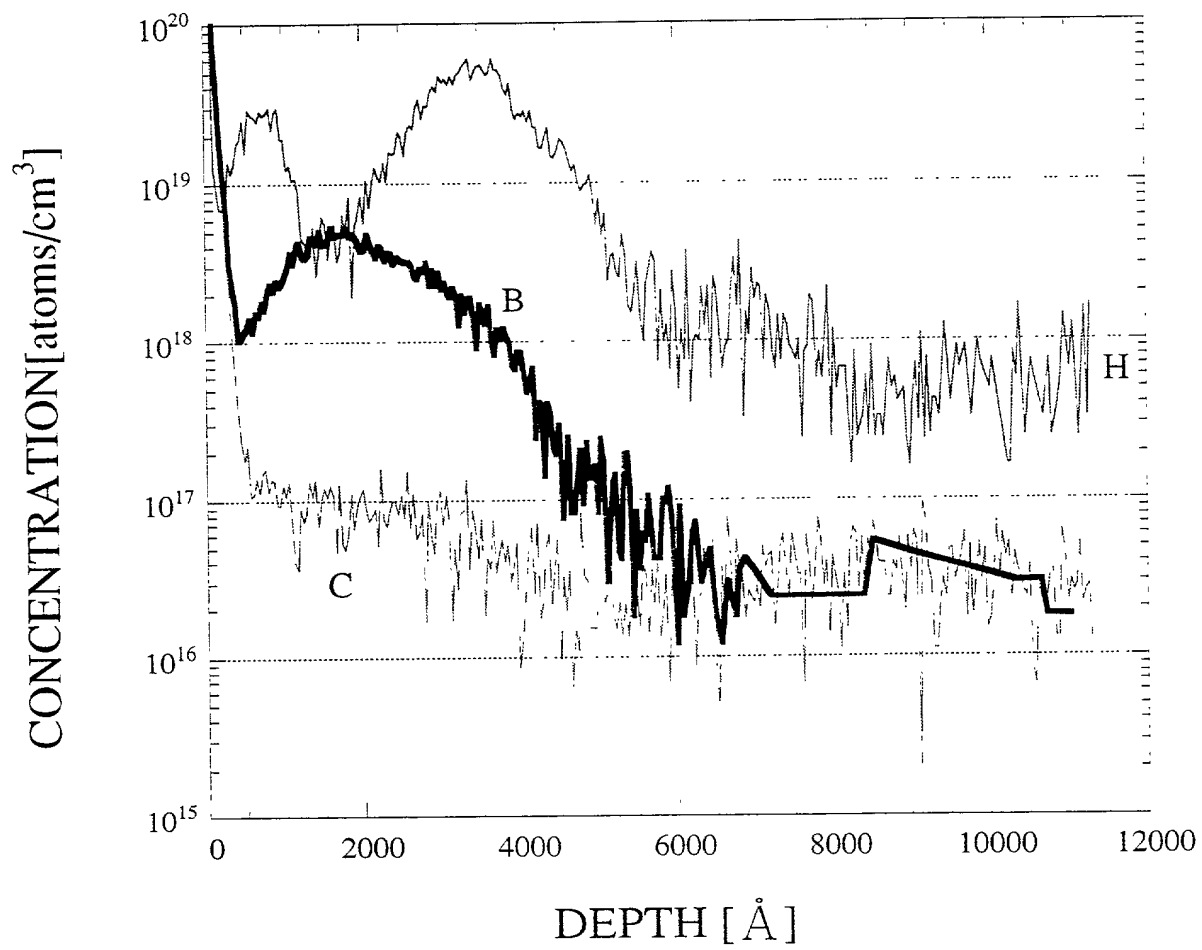


Fig. 1

TEST0-TH91.9/60

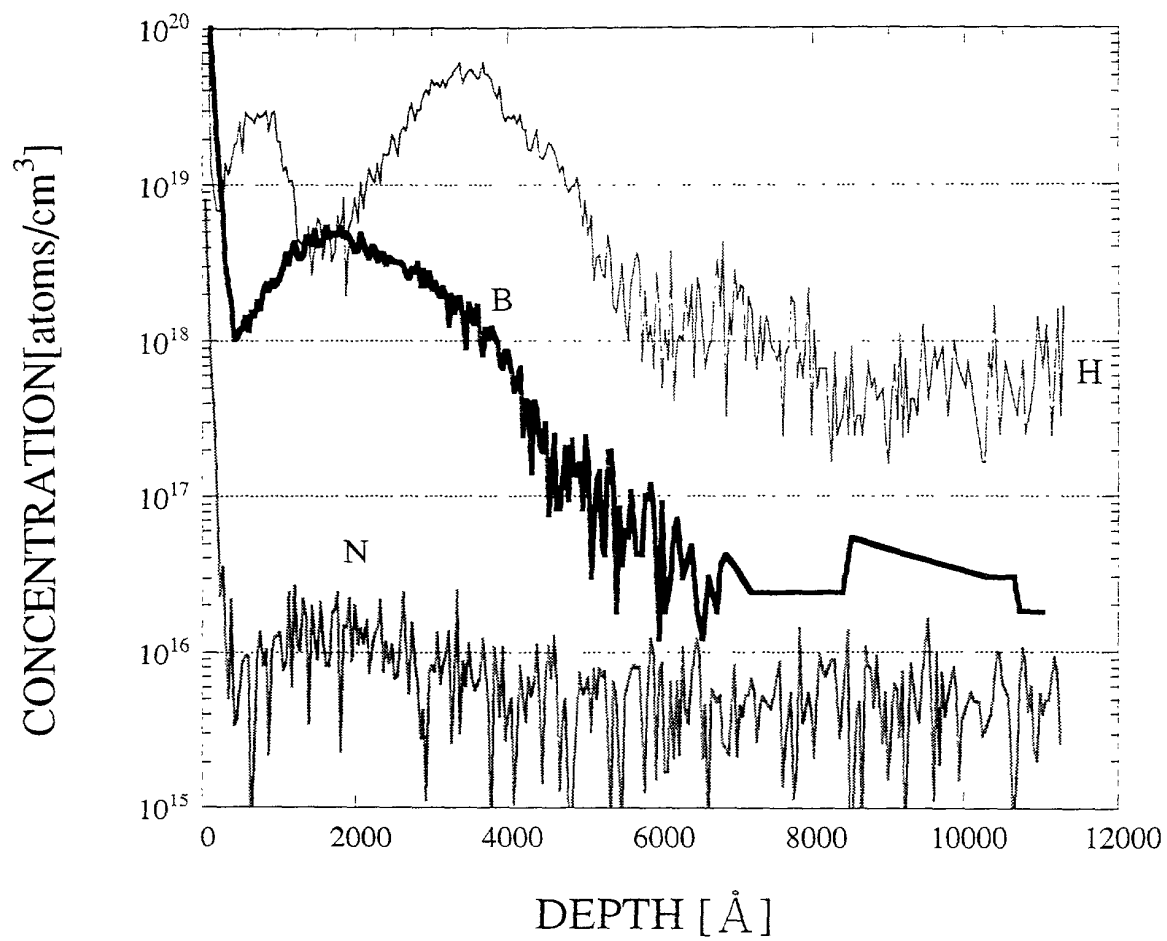


Fig. 2

FOOT-4379260

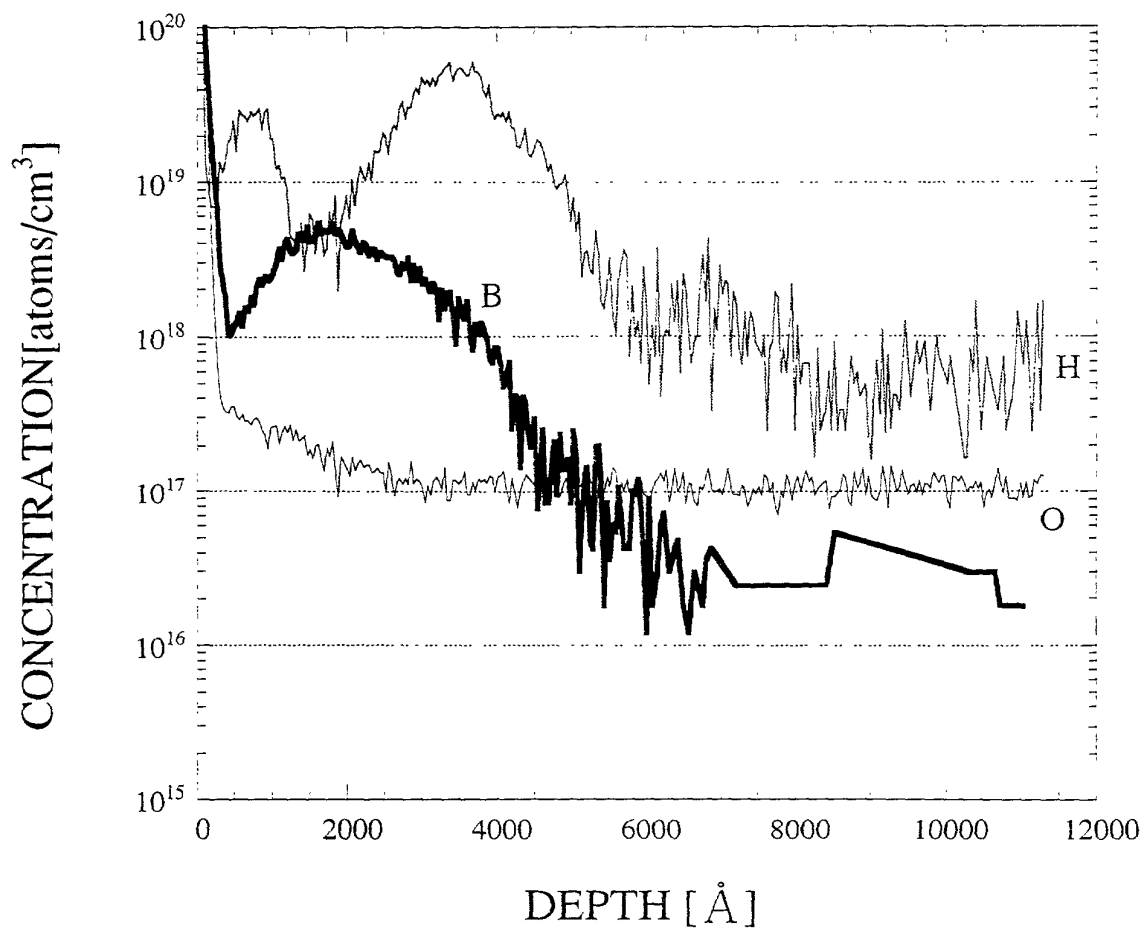


Fig. 3

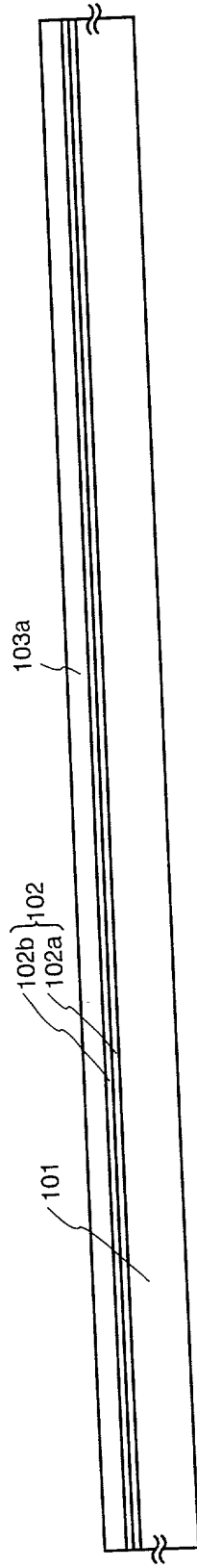


Fig. 4A

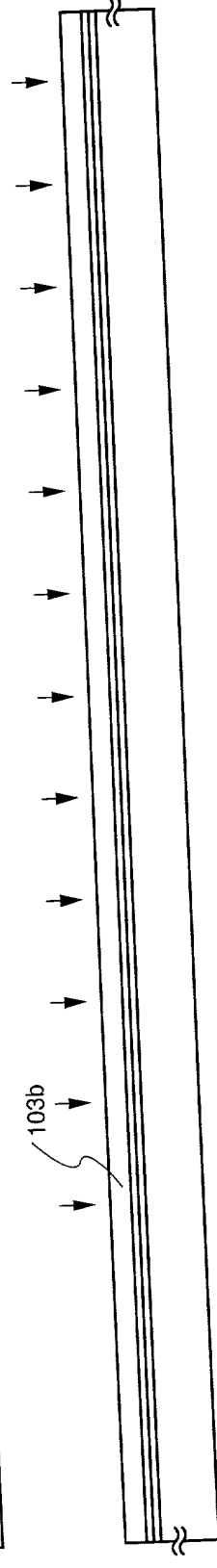


Fig. 4B

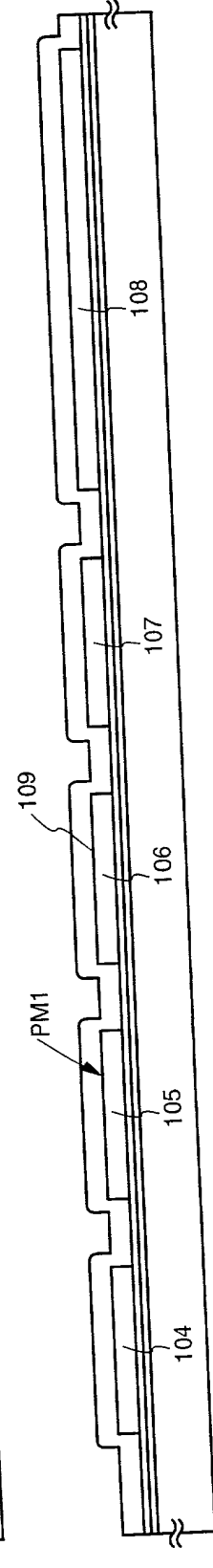


Fig. 4C

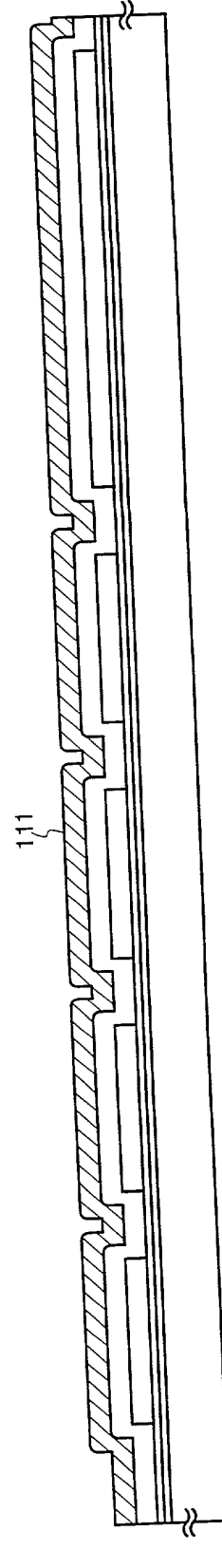


Fig. 4D

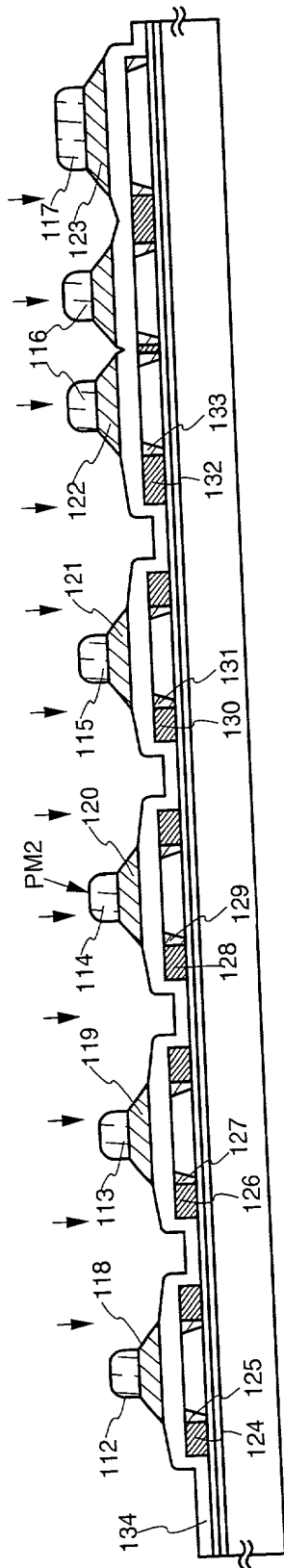


Fig. 5A

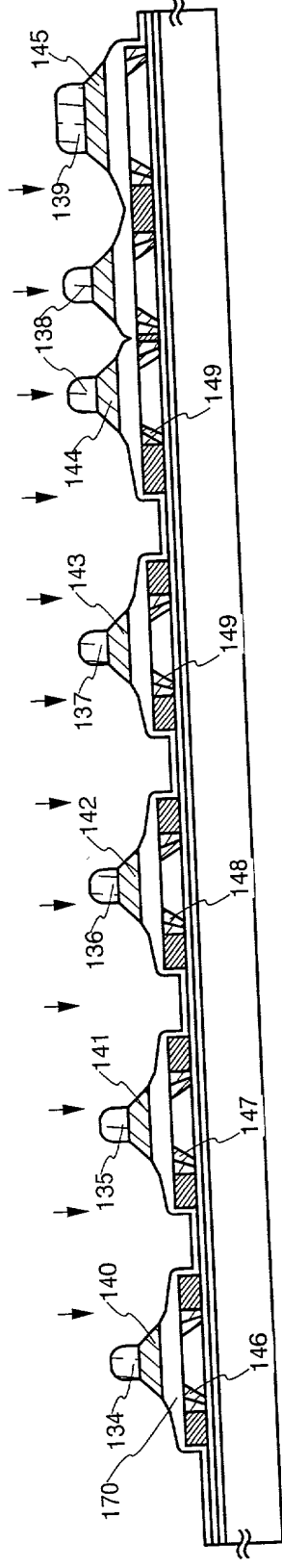


Fig. 5B

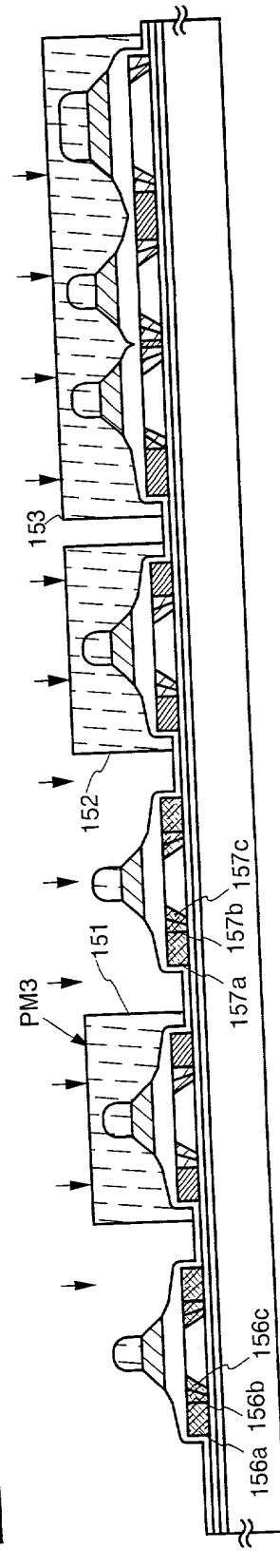


Fig. 5C

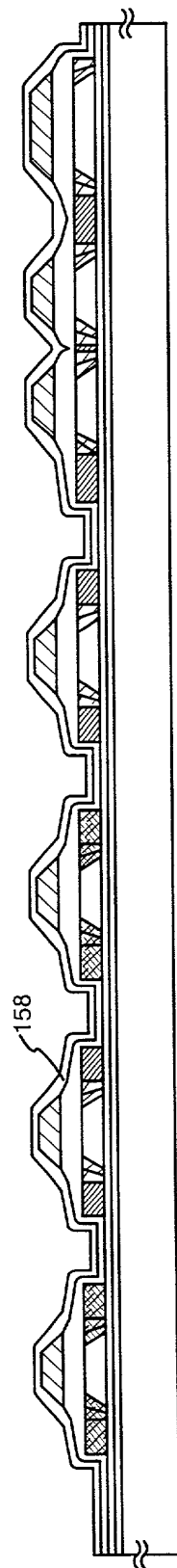


Fig. 6A

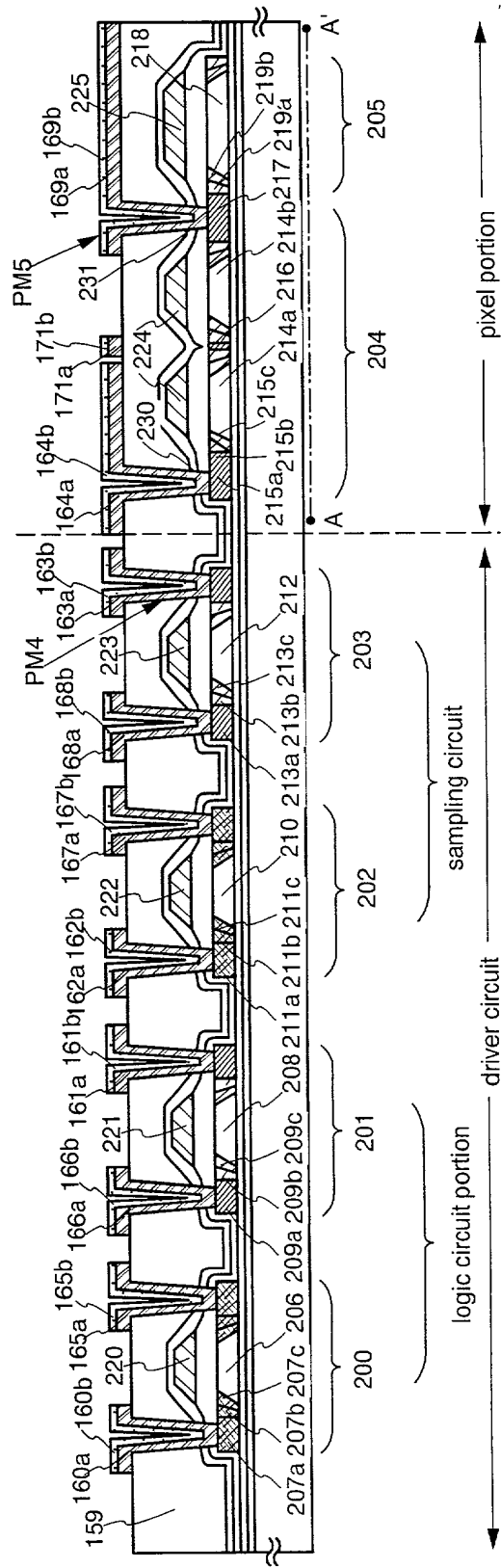


Fig. 6B

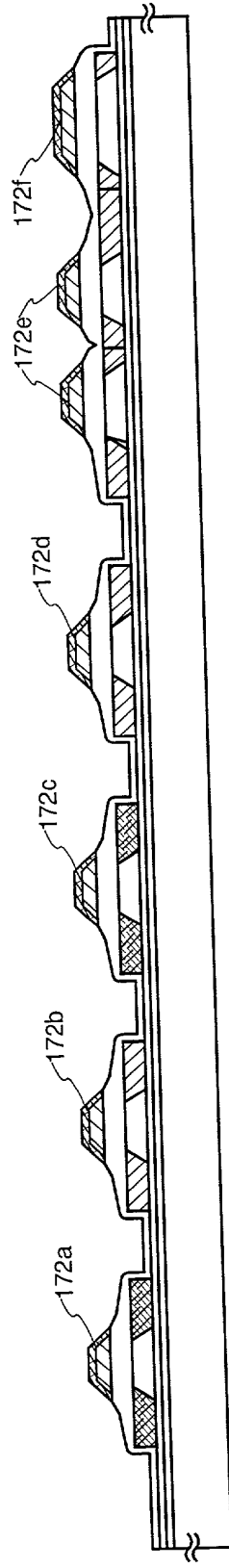


Fig. 7A

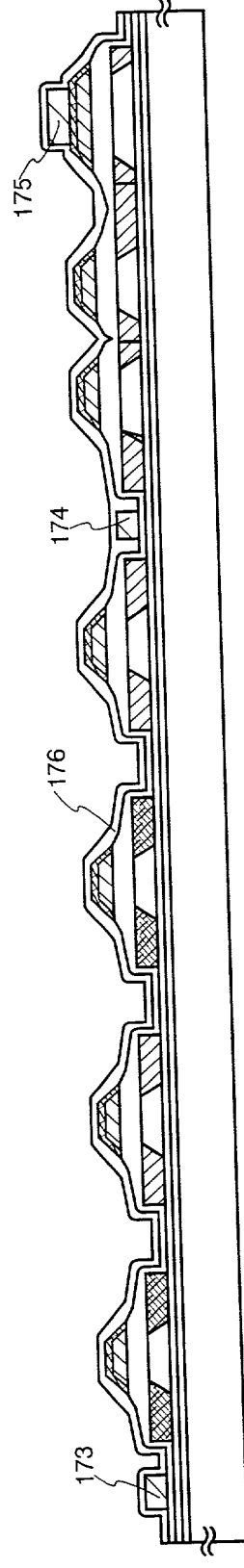


Fig. 7B

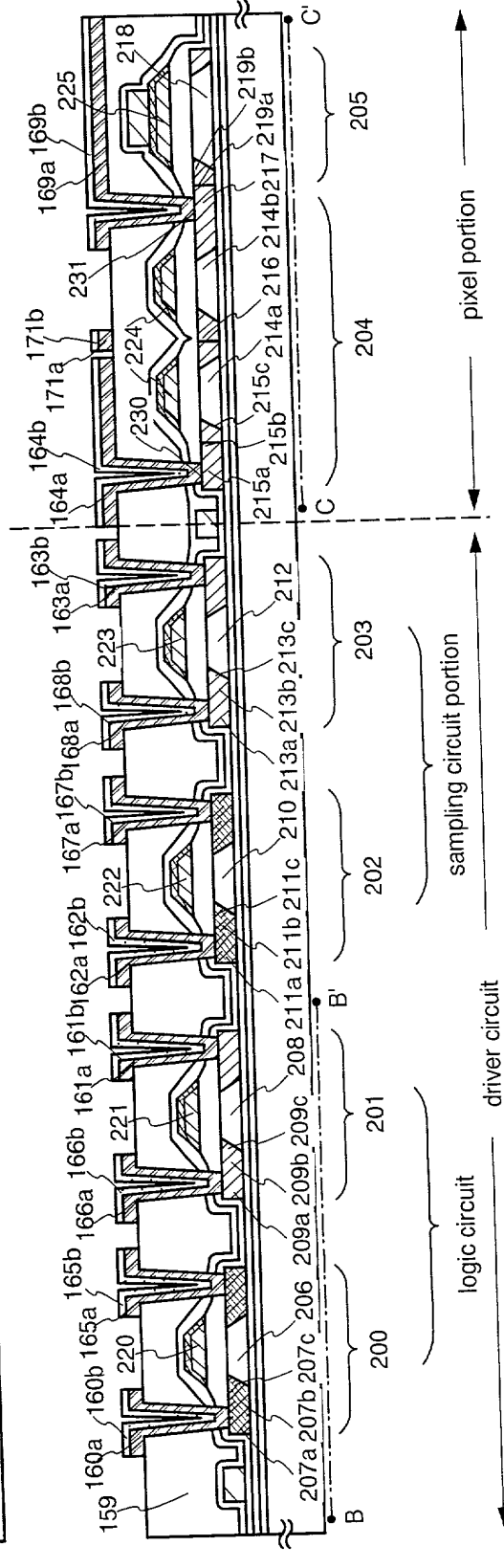


Fig. 7C

Fig. 8A

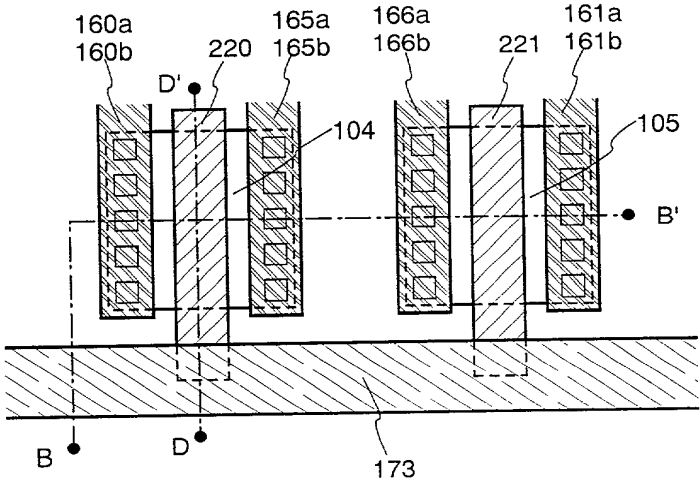


Fig. 8B

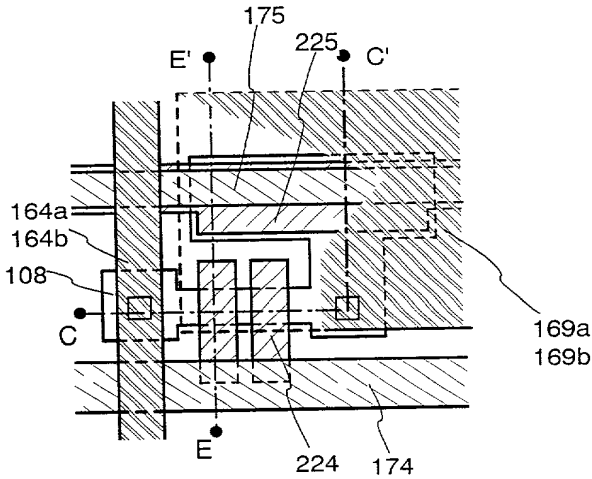


Fig. 9A

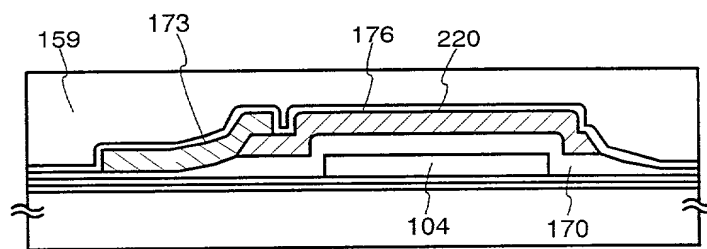


Fig. 9B

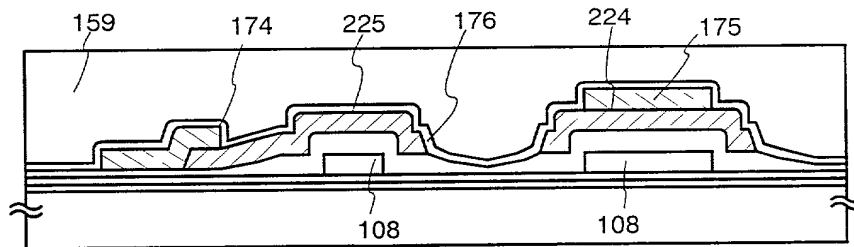


Fig. 10A

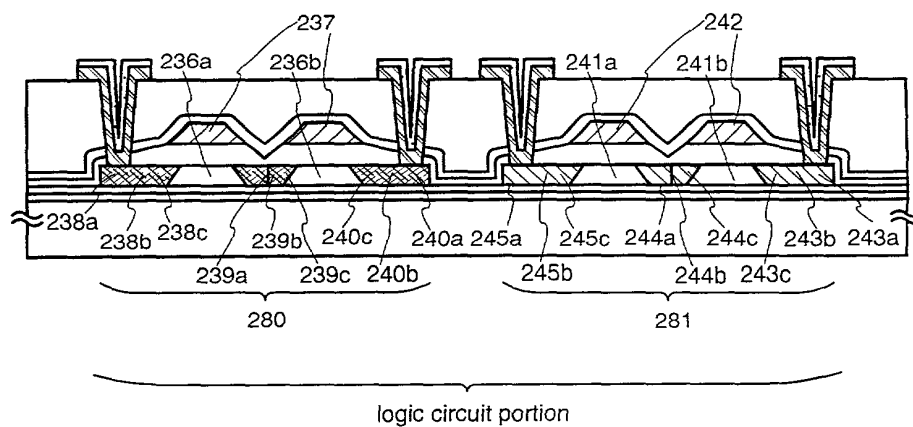


Fig. 10B

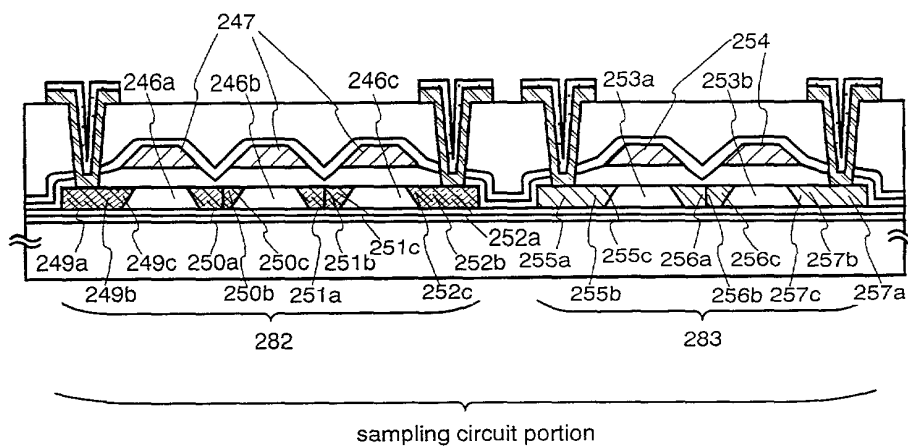


Fig. 11A

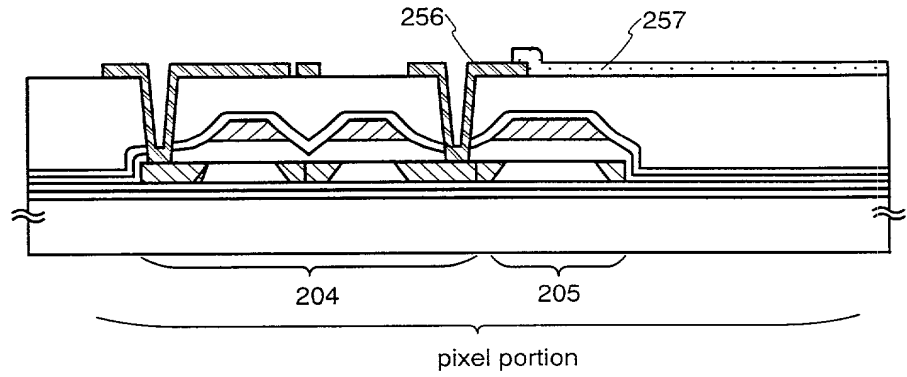


Fig. 11B

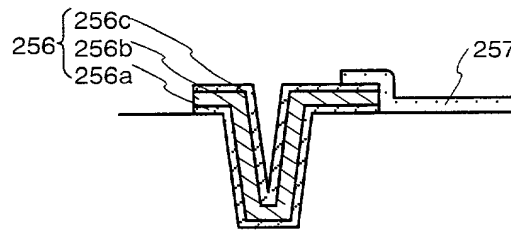


Fig. 11C

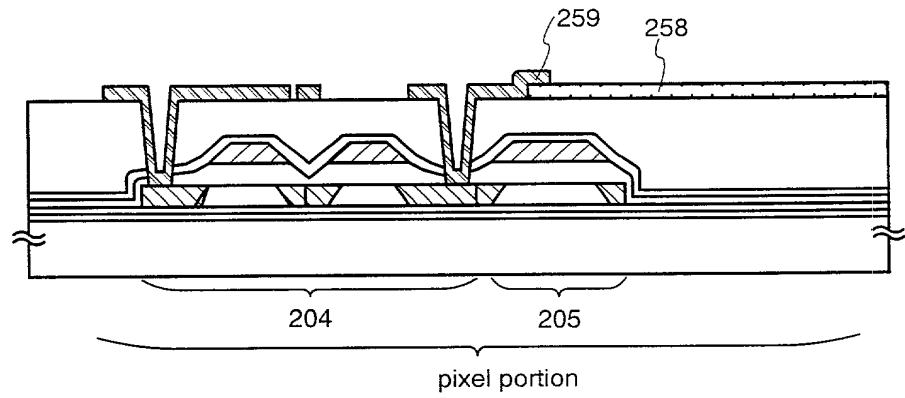
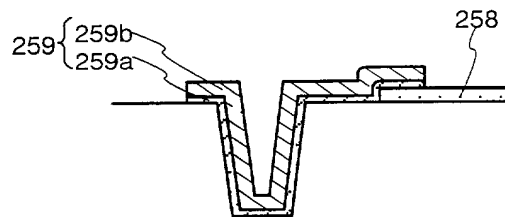


Fig. 11D



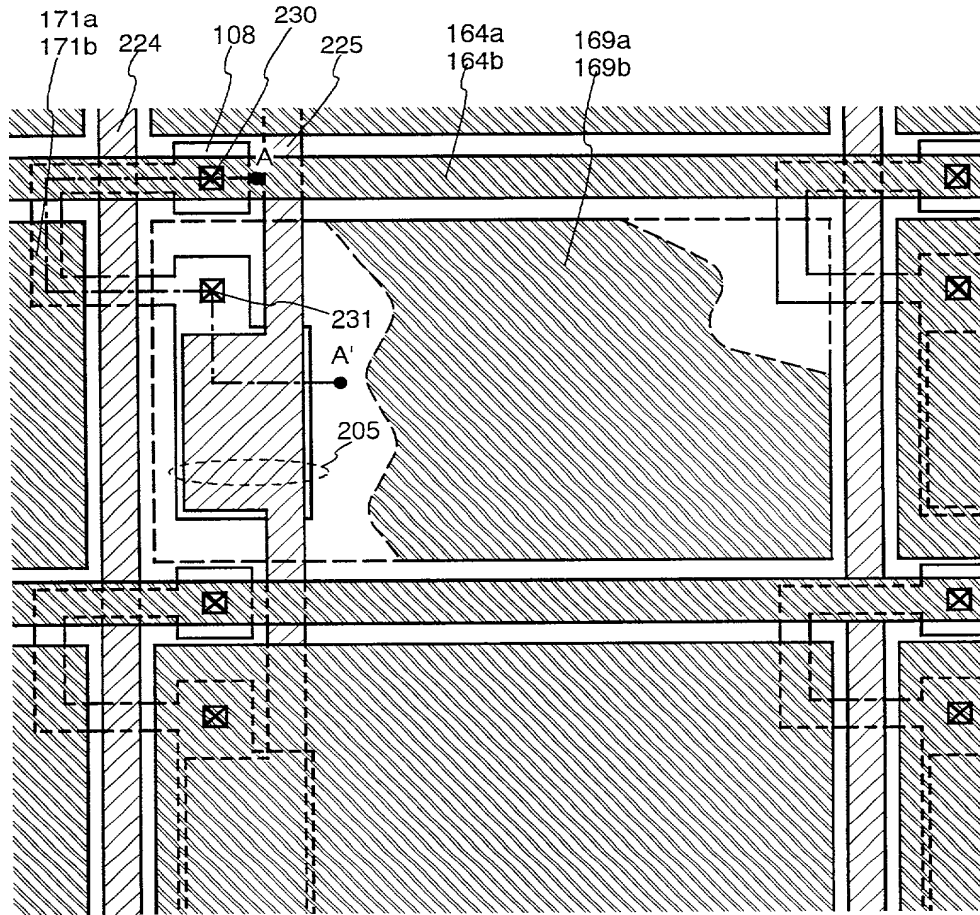
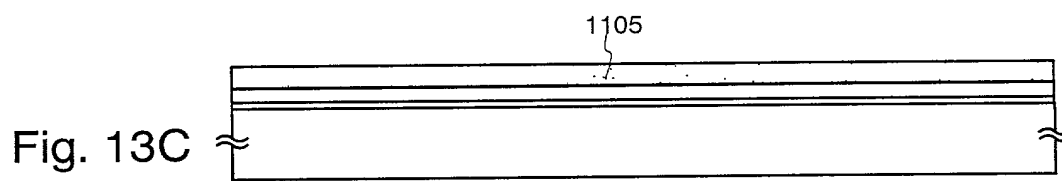
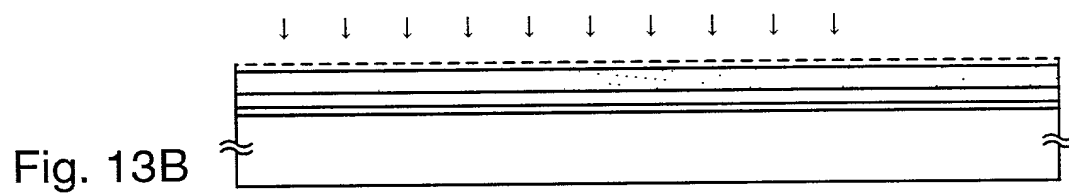
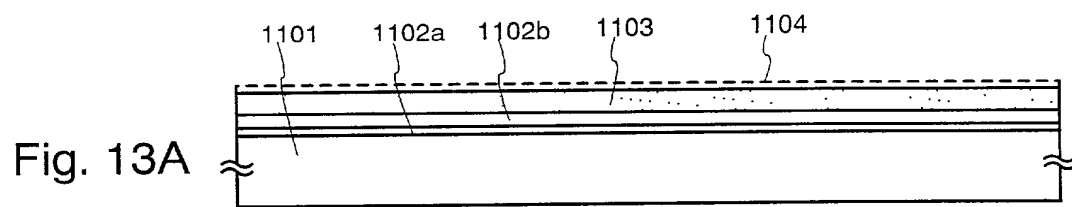
[illegible]

Fig. 12



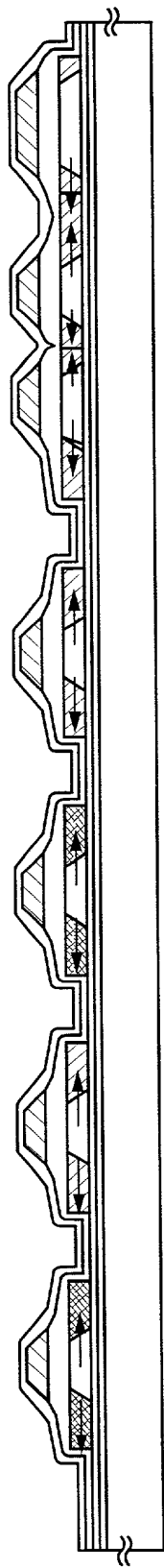


Fig. 14

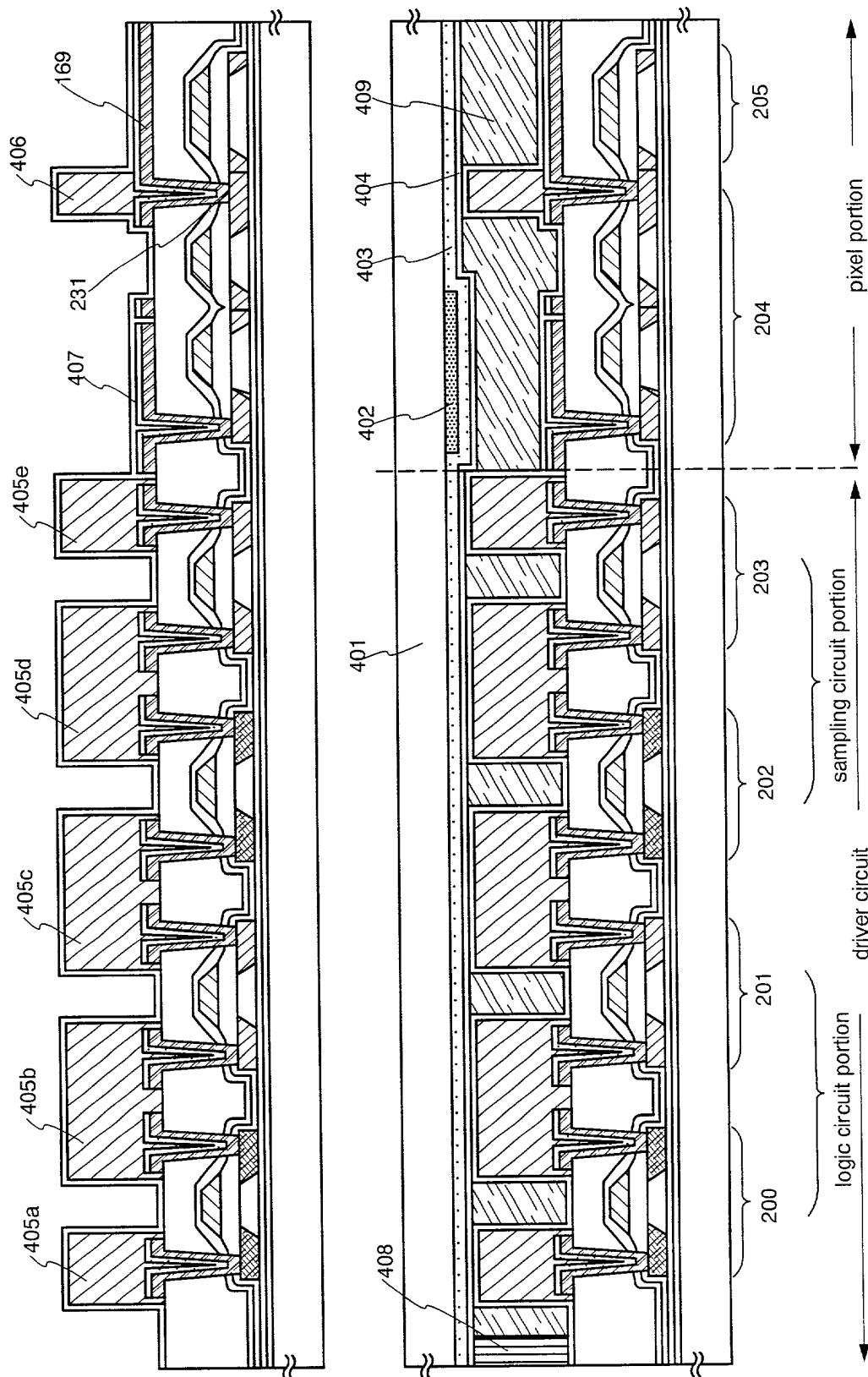


Fig. 15

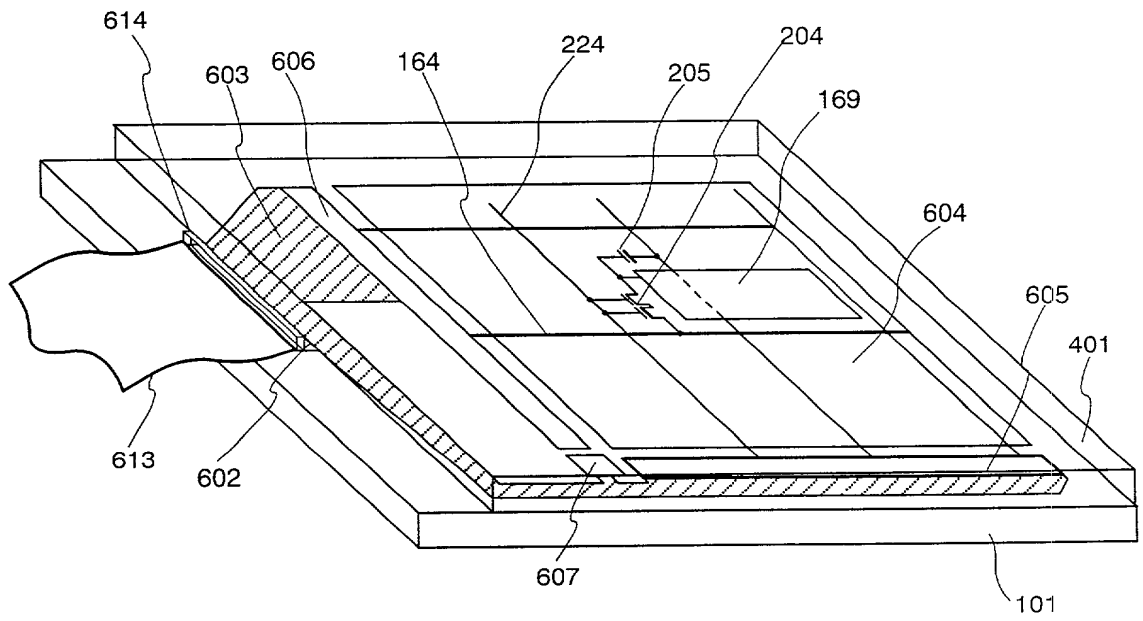


Fig. 16

Fig. 17A

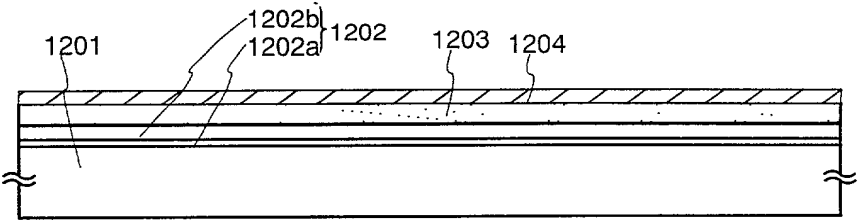


Fig. 17B

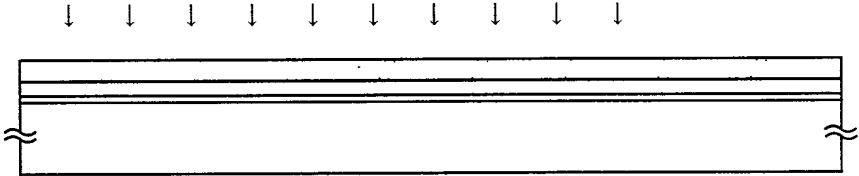
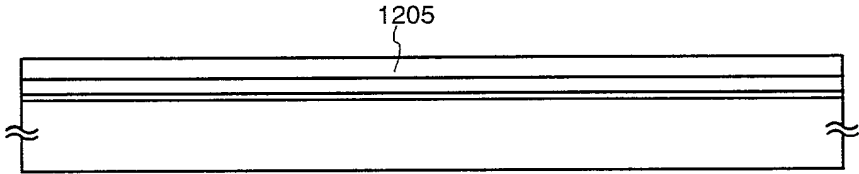


Fig. 17C



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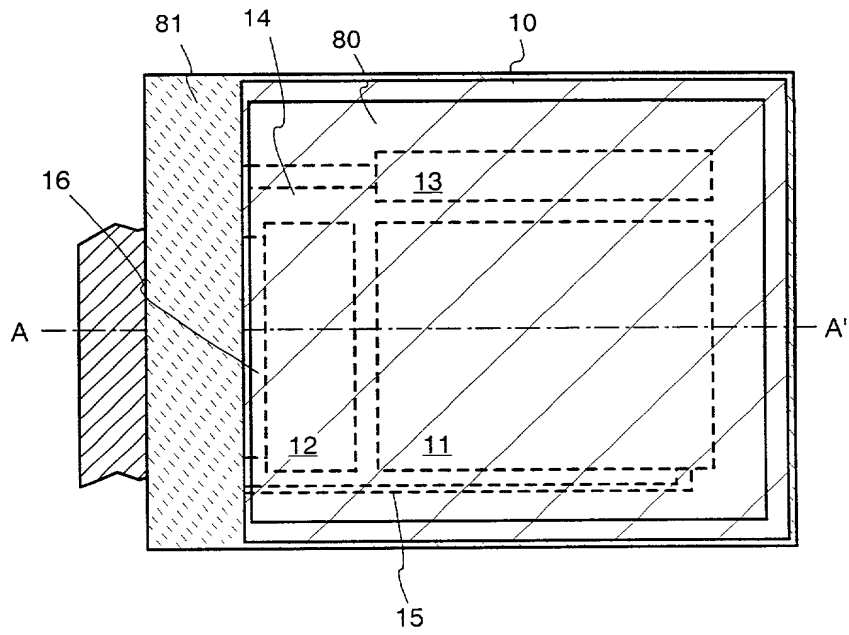


Fig. 18A

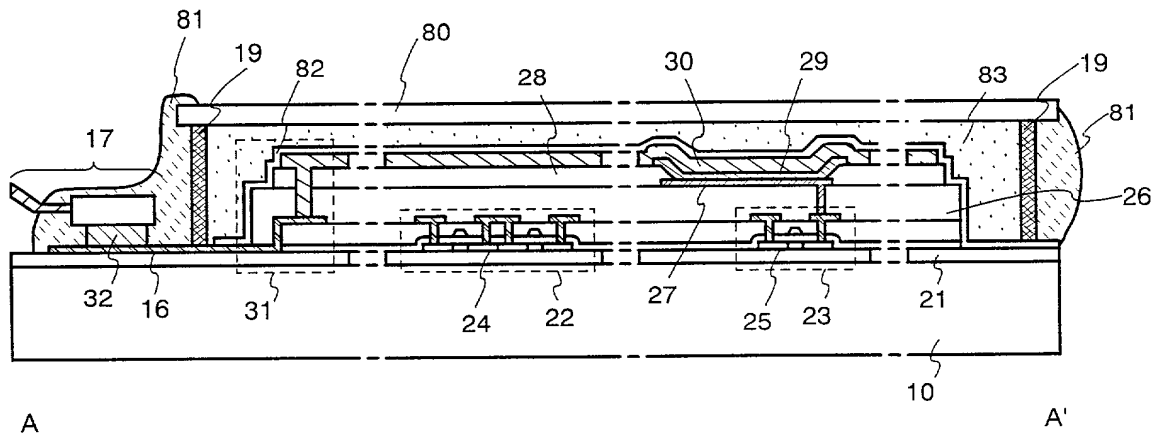


Fig. 18B

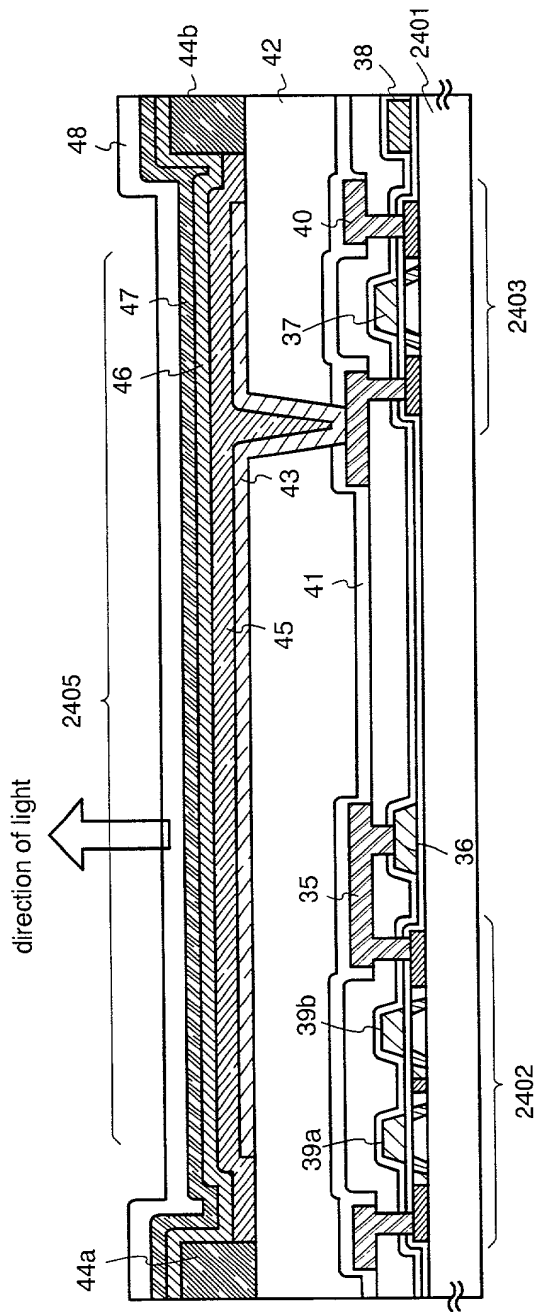


Fig. 19A

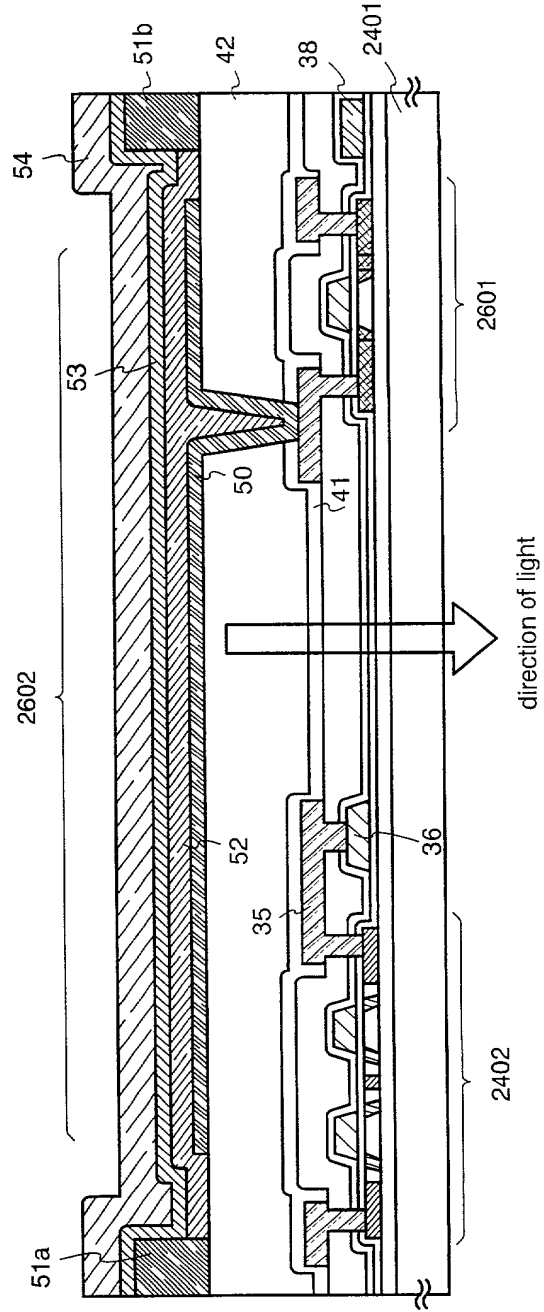


Fig. 19B

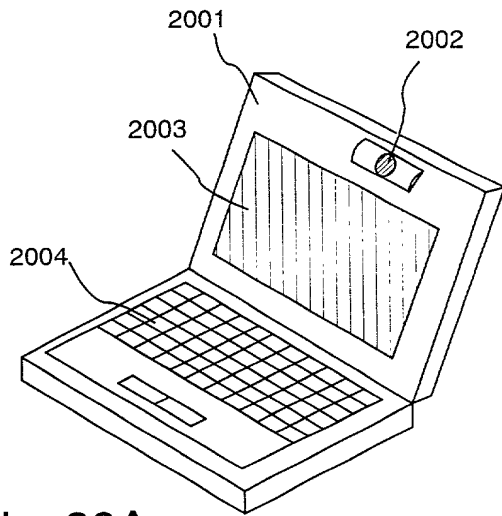


Fig. 20A

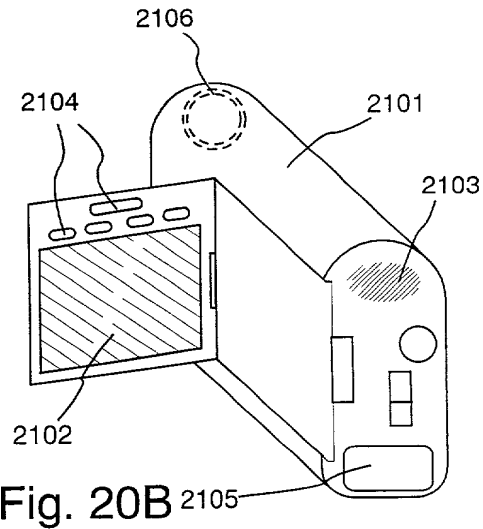


Fig. 20B

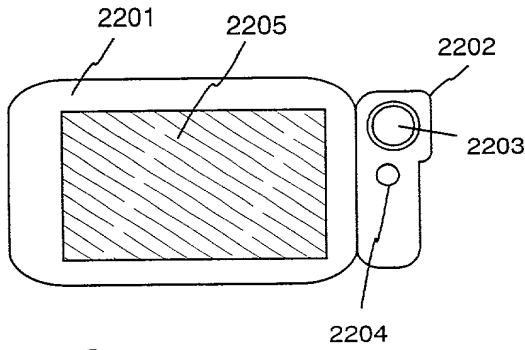


Fig. 20C

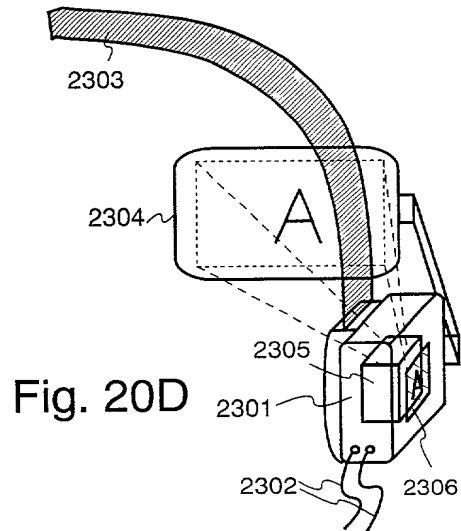


Fig. 20D

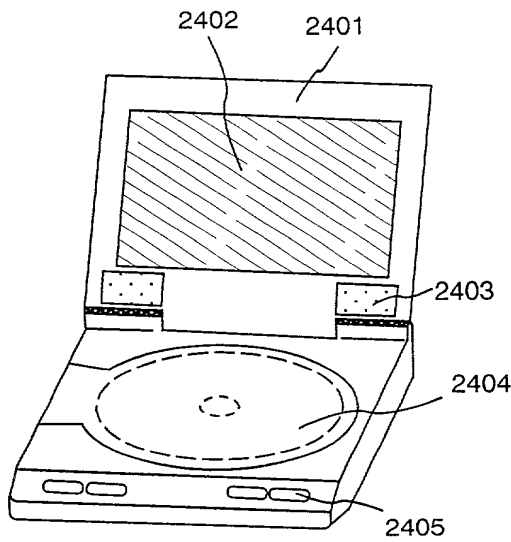


Fig. 20E

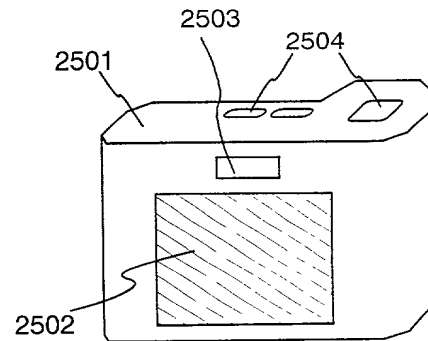


Fig. 20F

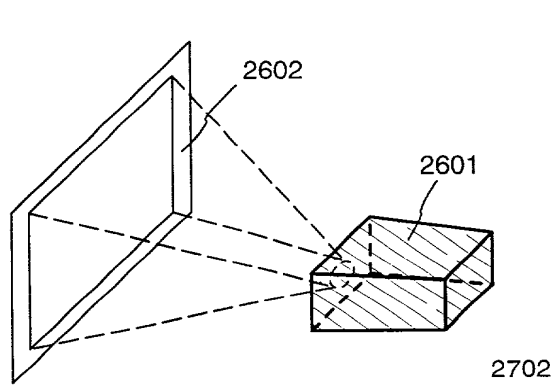


Fig. 21A

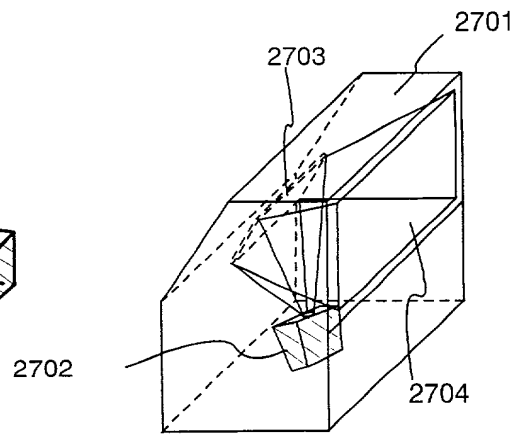


Fig. 21B

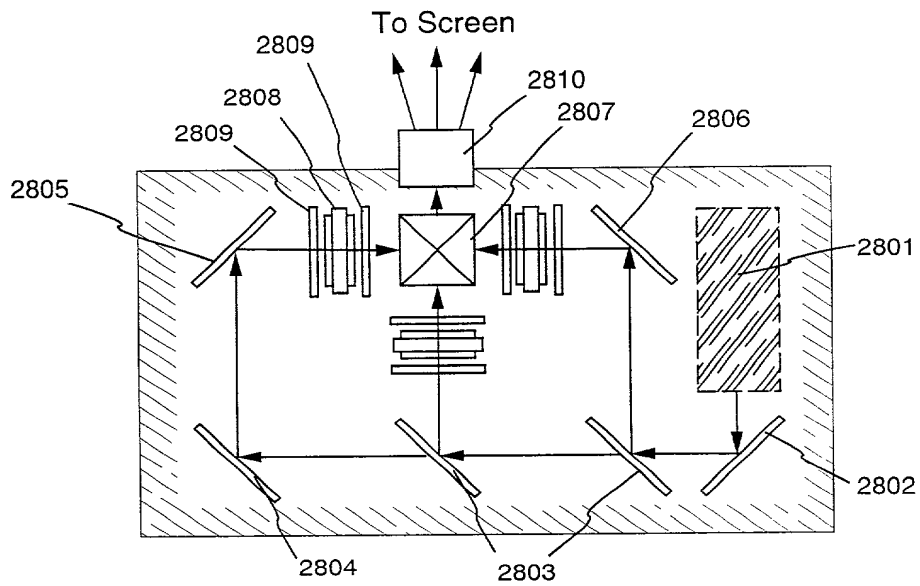


Fig. 21C

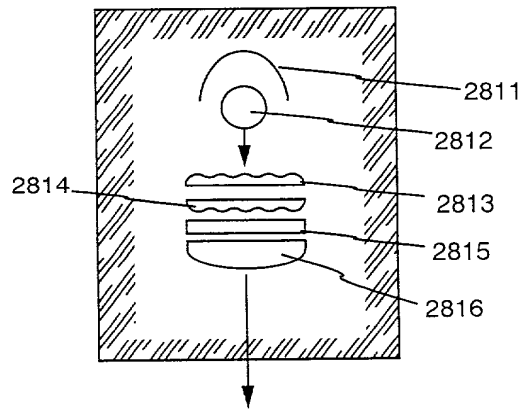


Fig. 21D

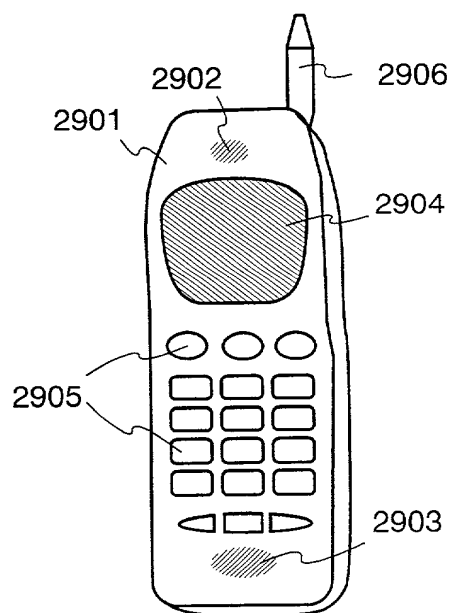


Fig. 22A

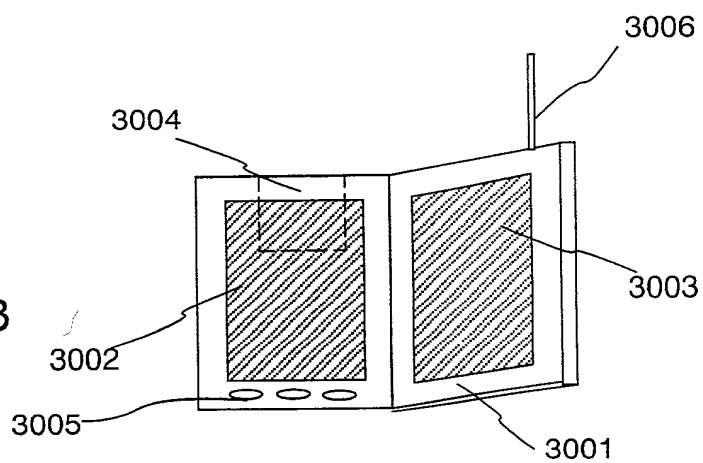


Fig. 22B

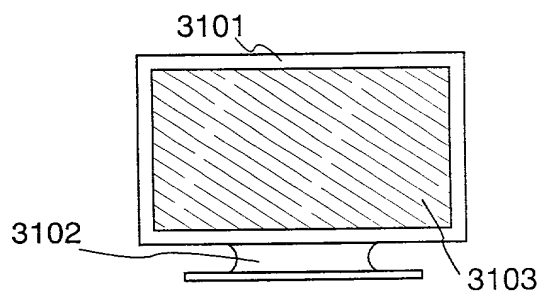


Fig. 22C

TOP: 11/11/2000

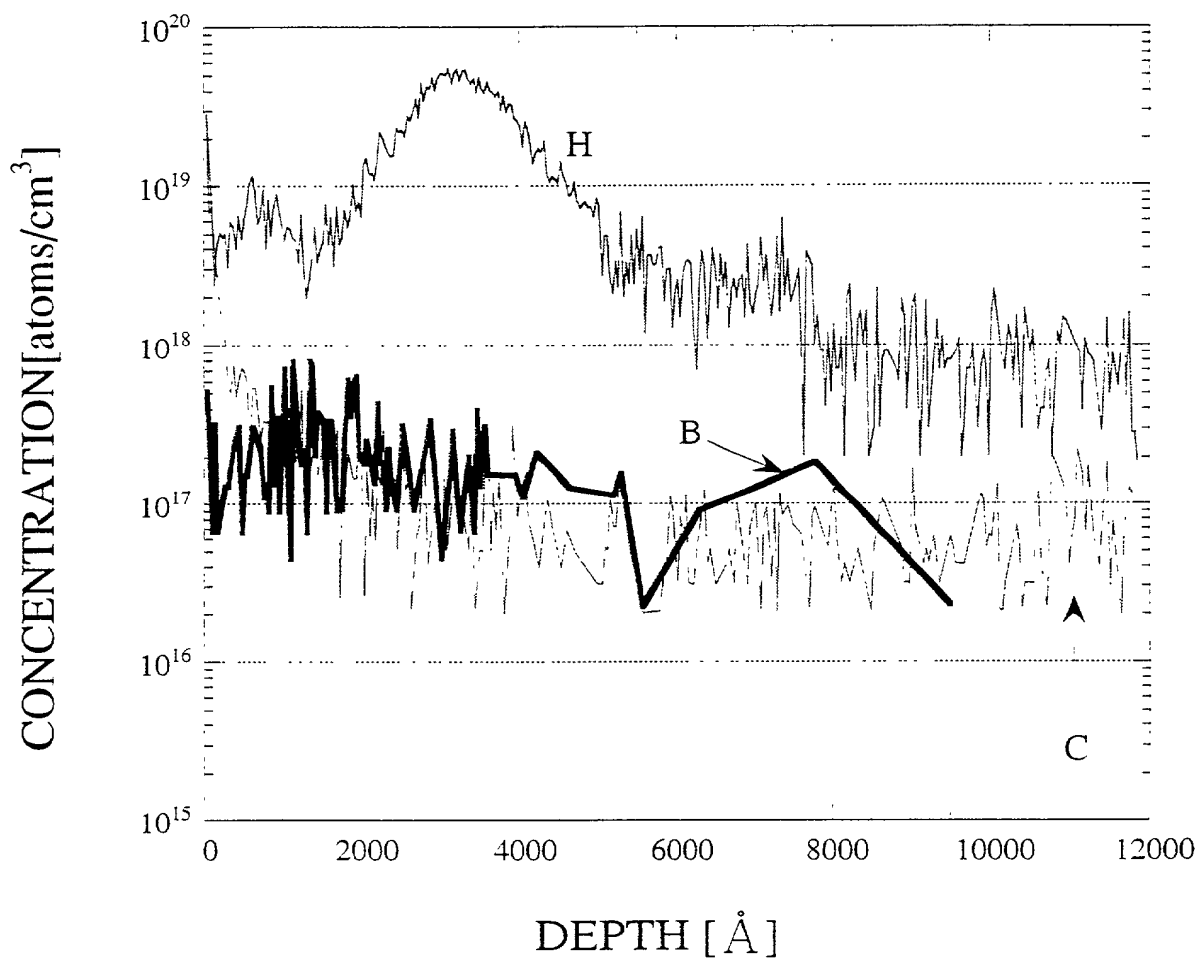


Fig. 23

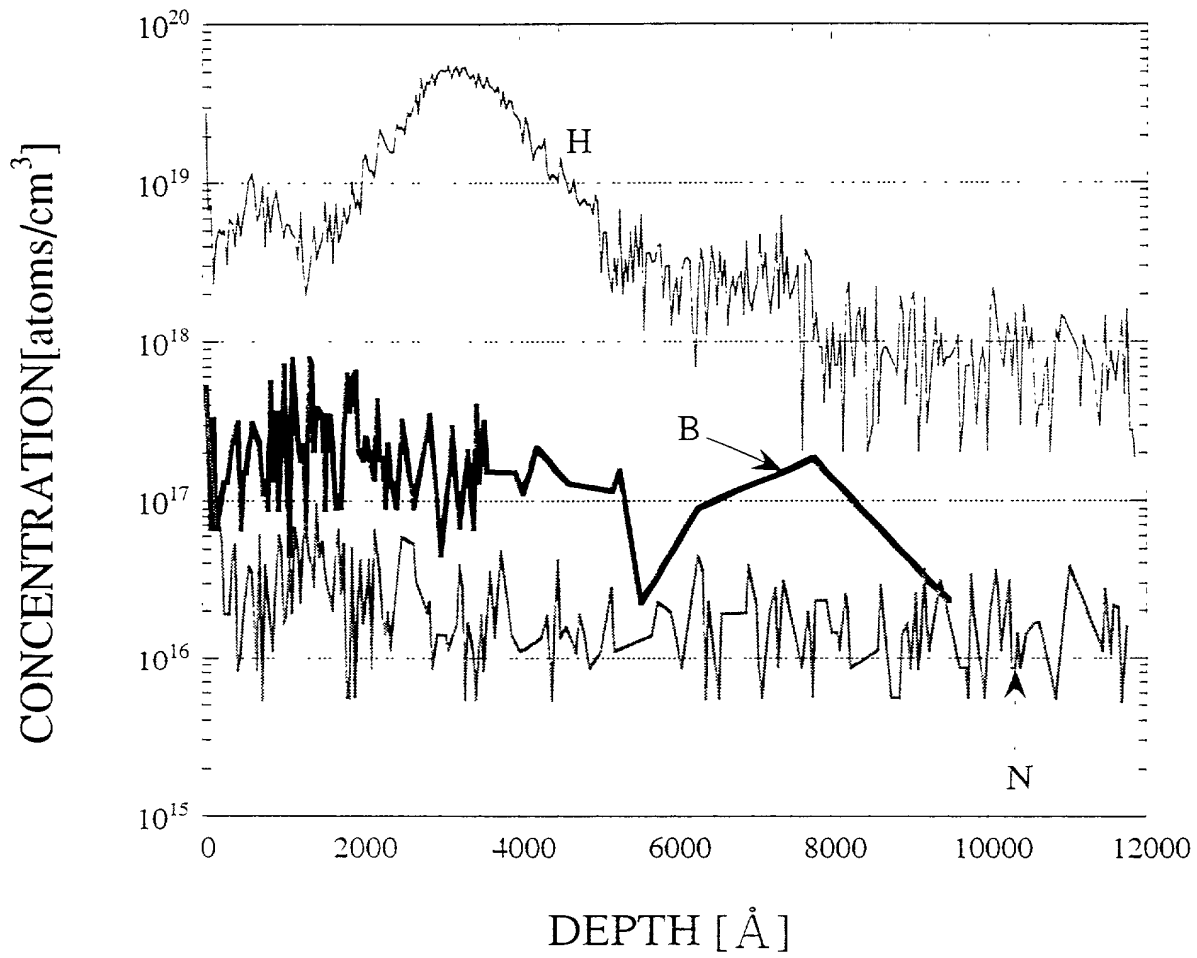


Fig. 24

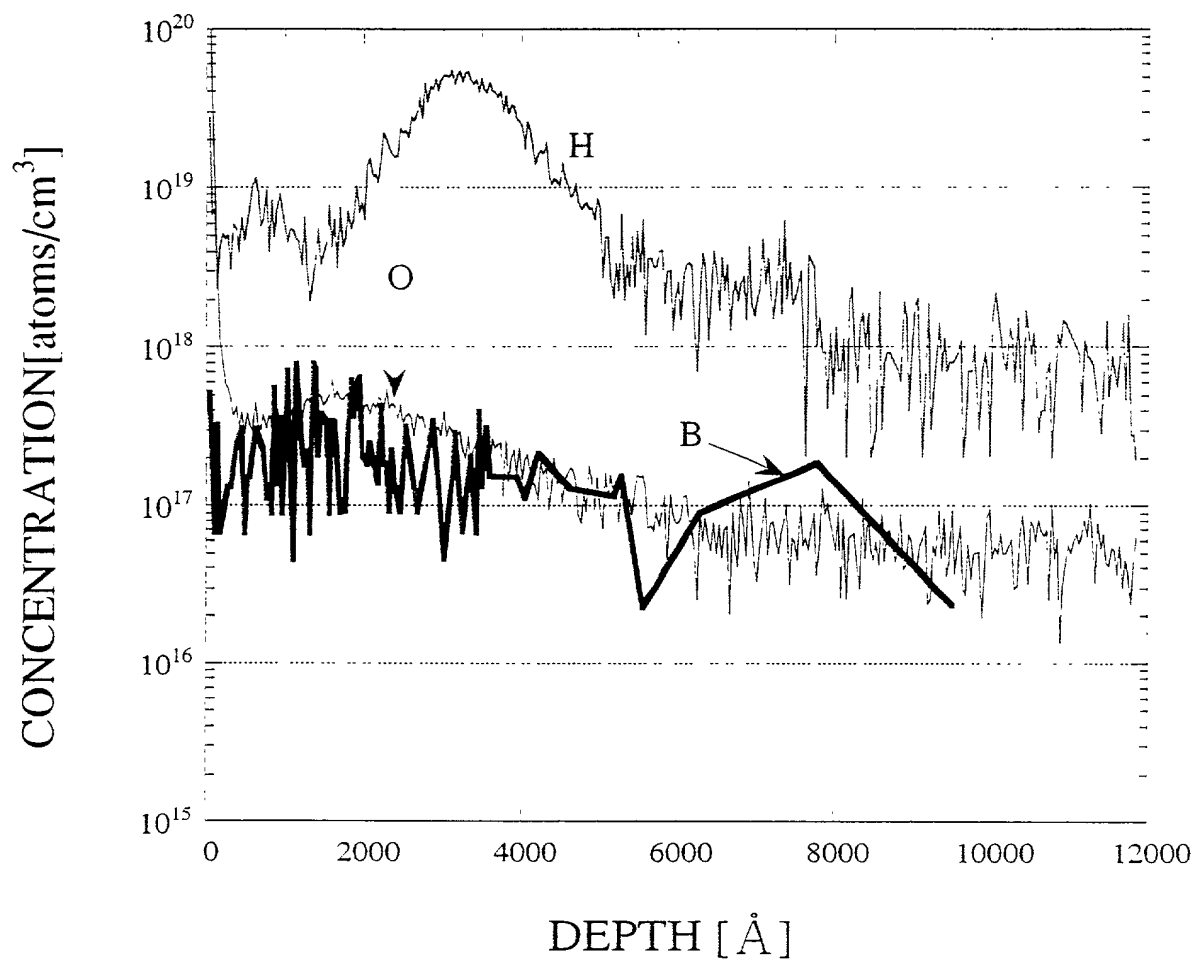


Fig. 25

Fig. 26

Fig. 27

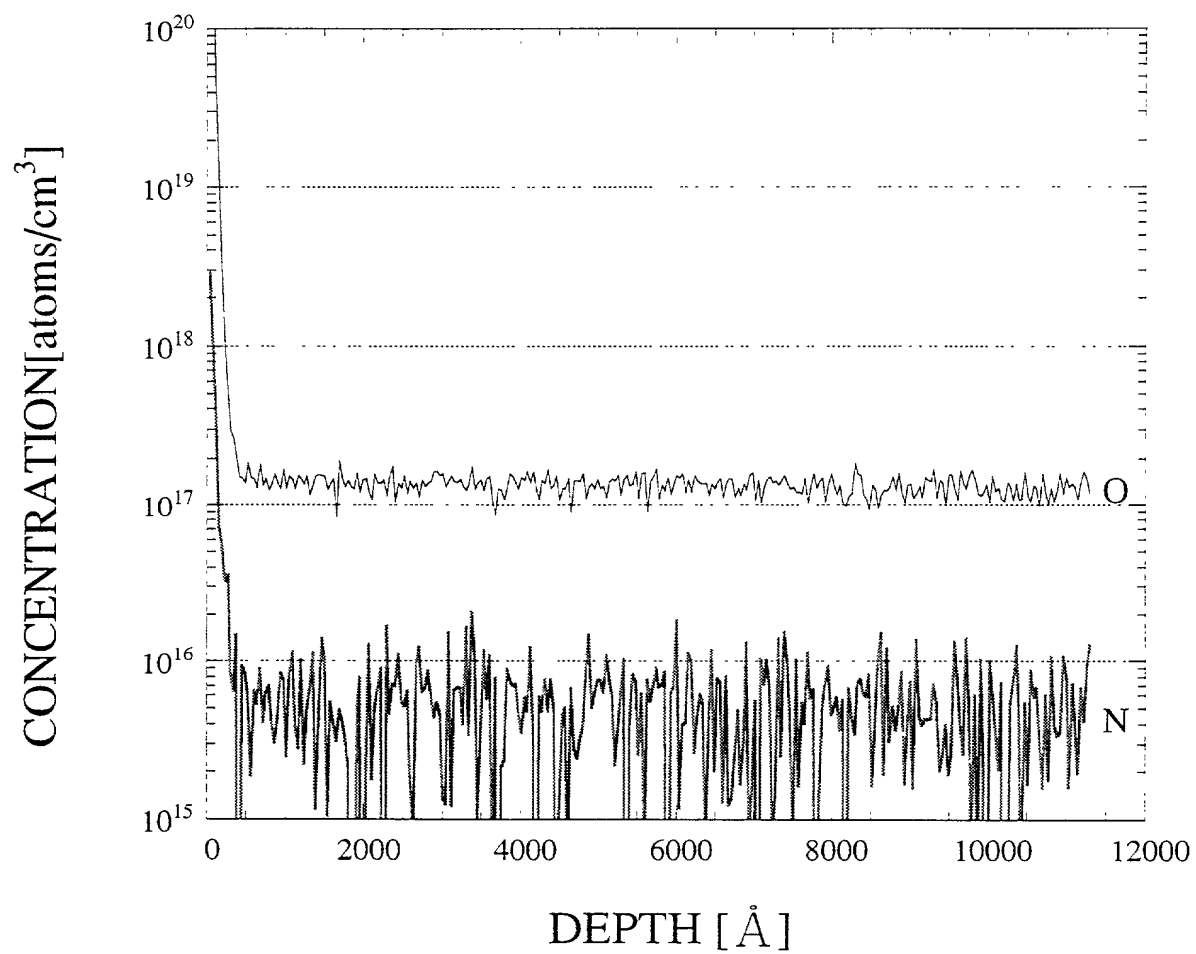
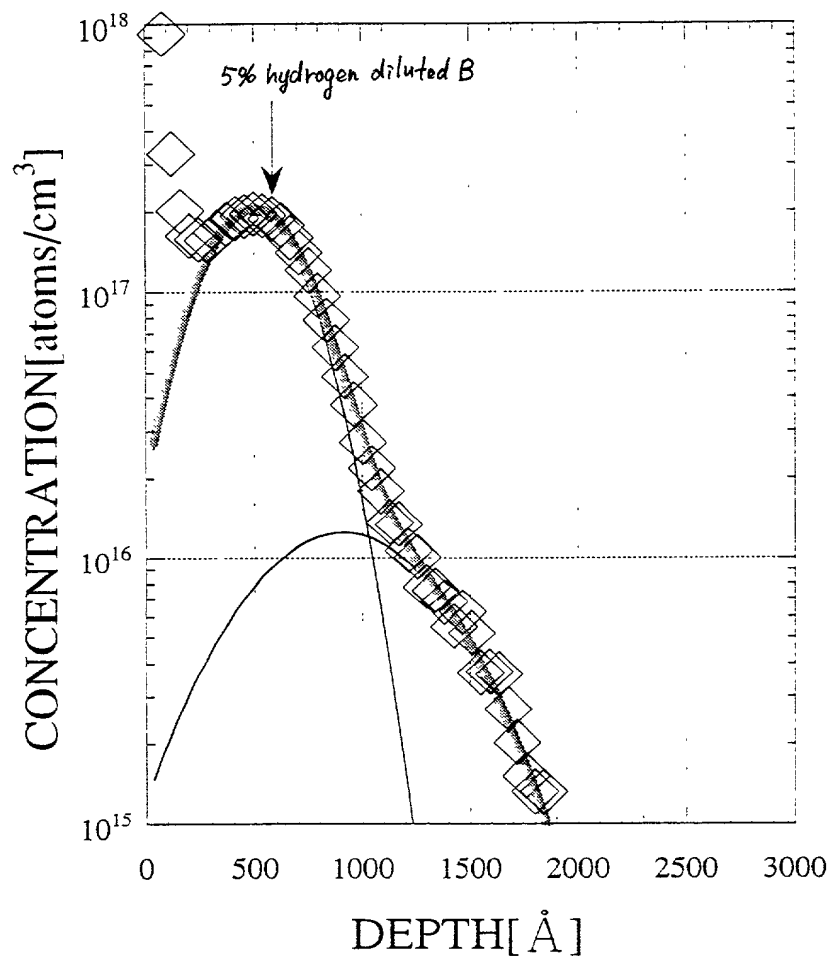


Fig. 28

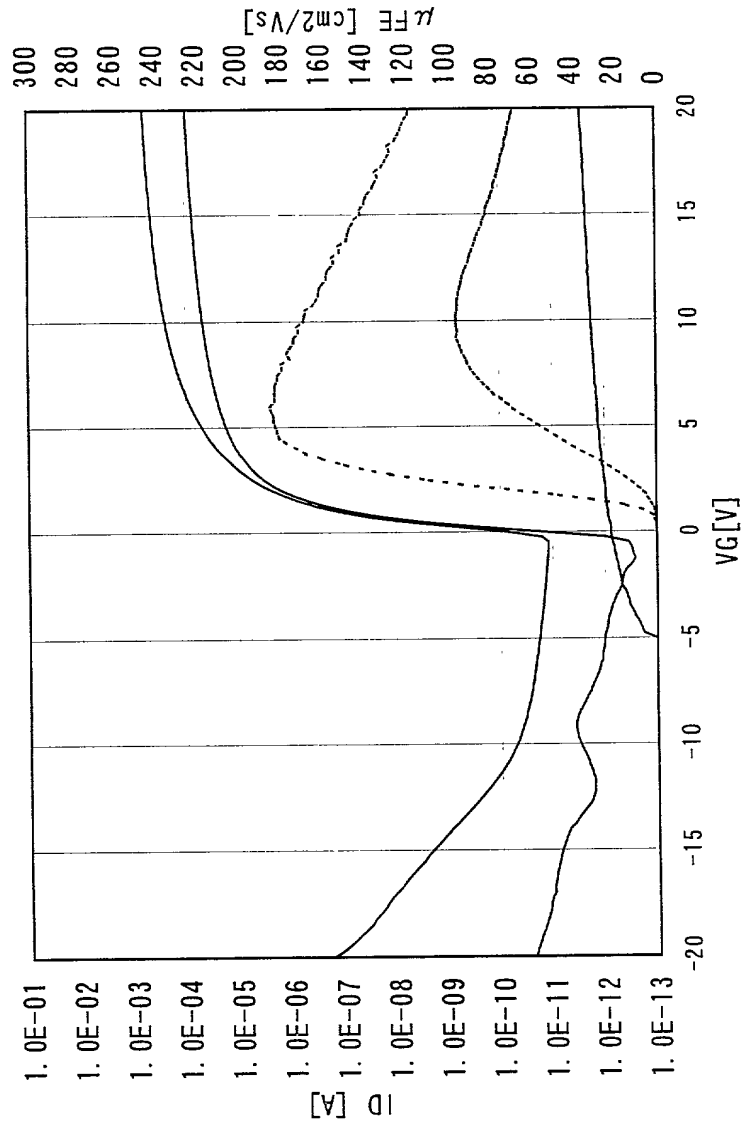


5% B fitting	
	value
dosage 1	1.1224e+12
dosage 2	1.3183e+11
standard deviation 1	227.08
standard deviation 2	422.75
projected range 1	494.37
projected range 2	908.19
χ^2	0.52998
R	1

Gaussian function fitting
 projected range of B at 20kV (Å)
 LSS calculation (into Si or SiO₂)
 B⁺ : ~ 1000 Å
 B₂⁺ : ~ 500 Å

Fig. 29

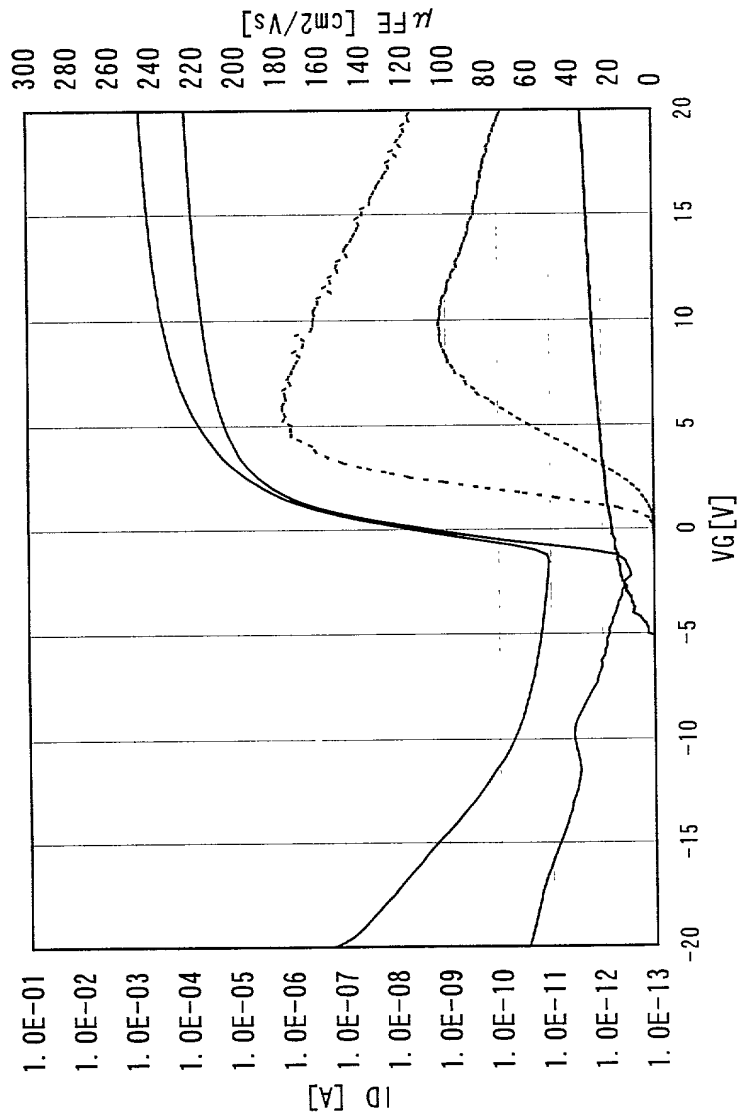
(N-ch, L/W= 7.1/ 7.5, Tox= 115)



parameter		N
channel type		A
kind of TFT		7.1
value of L [um]		7.5
value of W [um]		4.1
dielectric constant		115
thickness of oxide film [um]		
results		
Ion_2	2.44E-04	
[A]		
Ioff_2	1.70E-11	
[A]		
Shift_1[V]	-0.231	
Vth	1.430	
[V]		
S-value	0.201	
[V/dec]		
μ FE (max)	185.2	
[cm ² /Vs]		

Fig. 30

(N-ch, L/W= 7.1/ 7.5, Tox= 115)



parameters		N
channel type		A
kind of TFT		7.1
value of L [μm]		7.5
value of W [μm]		4.1
dielectric constant		115
thickness of oxide film [nm]		
results		
Ion_2	2.65E-04	
[A]		
Ioff_2	1.43E-11	
[A]		
Shift_1[V]	-1.086	
Vth	1.361	
[V]		
S-value	0.308	
[V/dec]		
$\mu_{FE}(\text{max})$	178.5	
[cm^2/Vs]		

Fig. 31